

ABSTRACT

Using a lower electrode as a photomask, a yophobic region having generally the same pattern as that of the lower electrode and a yophibic region having a pattern which is generally the inversion of the lower electrode pattern are formed on an insulating film. A conductive ink is applied to the yophobic region and baked. Thus, an upper electrode having a pattern which is generally the inversion of the lower electrode pattern is formed in a self-alignment manner. Therefore no misalignment occurs even if a printing method is used. Thus, a semiconductor device such as an active-matrix thin-film transistor substrate can be fabricated by using a printing method.